MAGNETORESISTIVE RANDOM ACCESS MEMORY (MRAM) CELL PATTERNING

Abstract of the Disclosure

A process that advantageously forms MRAM cells without the application of ion beam milling processes. Unlike conventional processes that rely on ion beam milling processes to remove materials from a magnetoresistive sandwich from areas other than areas that will later form MRAM cell bodies, this process forms a layer of photoresist over areas other than those areas that correspond to MRAM cell bodies. The photoresist is lifted off after the deposition of a magnetoresistive sandwich that forms the MRAM cell bodies, thereby safely removing the magnetoresistive sandwich from undesired areas while maintaining the magnetoresistive sandwich in the areas corresponding to MRAM cell bodies.

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